

# MC14551B

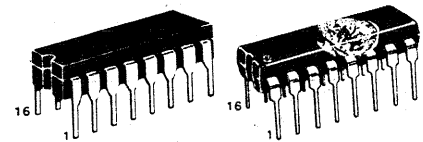
## CMOS MSI

(LOW-POWER COMPLEMENTARY MOS)

### QUAD 2-INPUT ANALOG MULTIPLEXER/ DEMULTIPLEXER

The MC14551B is a digitally controlled analog switch. It is an effective 4 PDT switch with low ON impedance and very low OFF leakage current. Control of analog signals up to the complete supply voltage range can be achieved.

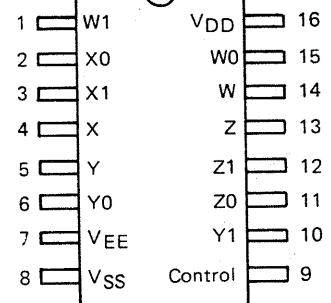
- High On/Off Output Ratio — 65 dB typical
- Quiescent Current = 5.0 nA/Package typical at 5 Vdc
- Low Crosstalk Between Switches — 80 dB typical
- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Analog Voltage Range ( $V_{DD}-V_{EE}$ ) = 3 to 18 V  
Note:  $V_{EE}$  must be  $\leq V_{SS}$
- Transmits Frequencies Up To 65 MHz
- Linearized Transfer Characteristics,  $\Delta R_{ON} < 60 \Omega$  for  $V_{in}$  at  $V_{DD}$  to  $V_{EE}$  at 15 Vdc
- Low Noise —  $12 \text{ nV}/\sqrt{\text{Cycle}}$ ,  $f \geq 1 \text{ kHz}$  typical



CASE 620  
L SUFFIX  
CERAMIC PACKAGE

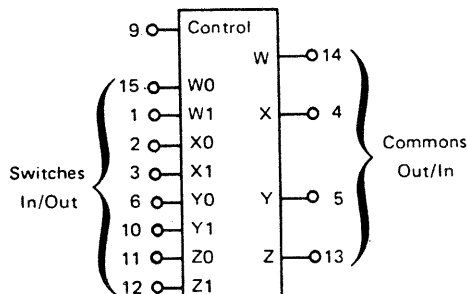
CASE 648  
P SUFFIX  
PLASTIC PACKAGE

#### PIN ASSIGNMENT



#### MAXIMUM RATINGS (Voltages referenced to $V_{SS}$ )

Rating	Symbol	Value	Unit
DC Supply Voltage $V_{DD} - V_{EE}$	$V_{DD}$	-0.5 to +18	Vdc
Input Voltage, All Inputs	$V_{in}$	-0.5 to $V_{DD} + 0.5$	Vdc
Through Current	I	25	mAdc
Operating Temperature Range	AL Device	$T_A$	$^{\circ}\text{C}$
	CL/CP Device		-55 to +125 -40 to +85
Storage Temperature Range	$T_{stg}$	-65 to +150	$^{\circ}\text{C}$



Control	ON
0	W0 X0 Y0 Z0
1	W1 X1 Y1 Z1

$V_{DD}$  = Pin 16  
 $V_{SS}$  = Pin 8  
 $V_{EE}$  = Pin 7

Note: Control Input referenced to  $V_{SS}$ . Analog Inputs and Outputs reference to  $V_{EE}$ .  $V_{EE}$  must be  $\leq V_{SS}$ .

ELECTRICAL CHARACTERISTICS (V<sub>EE</sub> = V<sub>SS</sub>)

Characteristic	Symbol	V <sub>DD</sub> Vdc	T <sub>low</sub> *		25°C			T <sub>high</sub> *		Unit
			Min	Max	Min	Typ	Max	Min	Max	
Output Voltage "0" Level V <sub>in</sub> = V <sub>DD</sub> or 0  "1" Level V <sub>in</sub> = 0 or V <sub>DD</sub>	V <sub>OL</sub>	5.0	—	0.05	—	0	0.05	—	0.05	Vdc
		10	—	0.05	—	0	0.05	—	0.05	
		15	—	0.05	—	0	0.05	—	0.05	
	V <sub>OH</sub>	5.0	4.95	—	4.95	5.0	—	4.95	—	Vdc
		10	9.95	—	9.95	10	—	9.95	—	
		15	14.95	—	14.95	15	—	14.95	—	
Input Voltage (Control) "0" Level (V <sub>O</sub> = 4.5 or 0.5 Vdc) (V <sub>O</sub> = 9.0 or 1.0 Vdc) (V <sub>O</sub> = 13.5 or 1.5 Vdc)  "1" Level (V <sub>O</sub> = 0.5 or 4.5 Vdc) (V <sub>O</sub> = 1.0 or 9.0 Vdc) (V <sub>O</sub> = 1.5 or 13.5 Vdc)	V <sub>IL</sub>	5.0	—	1.5	—	2.25	1.5	—	1.5	Vdc
		10	—	3.0	—	4.50	3.0	—	3.0	
		15	—	4.0	—	6.75	4.0	—	4.0	
	V <sub>IH</sub>	5.0	3.5	—	3.5	2.75	—	3.5	—	Vdc
		10	7.0	—	7.0	5.50	—	7.0	—	
		15	11.0	—	11.0	8.25	—	11.0	—	
Input Current (Control) (AL Device)	I <sub>in</sub>	15	—	±0.1	—	±0.00001	±0.1	—	±1.0	µA <sub>dc</sub>
Input Current (Control) (CL/CP Device)	I <sub>in</sub>	15	—	±0.3	—	±0.00001	±0.3	—	±1.0	µA <sub>dc</sub>
Input Capacitance (V <sub>in</sub> = 0) Control, Inhibit Switch Inputs (Inhibit = 1)	C <sub>in</sub>	—	—	—	—	5.0	7.5	—	—	pF
		—	—	—	—	10	21.0	—	—	
Output Capacitance	C <sub>out</sub>	10	—	—	—	17	—	—	—	pf
Feedthrough Capacitance	C <sub>in-out</sub>	10	—	—	—	0.10	—	—	—	pF
Quiescent Current (AL Device) (Per Package)	I <sub>DD</sub>	5.0	—	5.0	—	0.005	5.0	—	150	µA <sub>dc</sub>
		10	—	10	—	0.010	10	—	300	
		15	—	20	—	0.015	20	—	600	
Quiescent Current (CL/CP Device) (Per Package)	I <sub>DD</sub>	5.0	—	20	—	0.005	20	—	150	µA <sub>dc</sub>
		10	—	40	—	0.010	40	—	300	
		15	—	80	—	0.015	80	—	600	
Total Supply Current**† (Dynamic plus Quiescent, Per Package)	I <sub>T</sub>	5.0	I <sub>T</sub> = (0.07 µA/kHz) f + I <sub>Q</sub>							µA <sub>dc</sub>
		10	I <sub>T</sub> = (0.20 µA/kHz) f + I <sub>Q</sub>							
		15	I <sub>T</sub> = (0.36 µA/kHz) f + I <sub>Q</sub>							
On Resistance (AL Device)	R <sub>ON</sub>	5.0	—	800	—	250	1050	—	1300	Ω
		10	—	400	—	120	500	—	550	
		15	—	220	—	80	280	—	320	
On Resistance (CL/CP Device)	R <sub>ON</sub>	5.0	—	880	—	250	1050	—	1200	Ω
		10	—	450	—	120	500	—	520	
		15	—	250	—	80	280	—	300	
Δ ON resistance Between Any Two Channels	Δ R <sub>ON</sub>	5.0	—	—	—	25	—	—	—	Ω
		10	—	—	—	10	—	—	—	
		15	—	—	—	5.0	—	—	—	
OFF Channel Leakage Current (AL Device) Any Channel All Channels OFF:	—	15	—	±100	—	±0.01	±100	—	±1000	nA <sub>dc</sub>
		15	—	±100	—	±0.02	±100	—	±1000	
OFF Channel Leakage Current (CL/CP Device) Any Channel All Channels OFF:	—	15	—	±300	—	±0.01	±300	—	±1000	nA <sub>dc</sub>
		15	—	±300	—	±0.02	±300	—	±1000	

\* T<sub>low</sub> = -55°C for AL Device, -40°C for CL/CP Device.

T<sub>high</sub> = +125°C for AL Device, +85°C for CL/CP Device.

Noise immunity is defined as the control input voltage coincident with the specified change, ΔV<sub>out</sub>, at an output in the OFF State.

\*\* The formulae given are for the typical characteristics only at 25°C.

† Total Supply Current, I<sub>T</sub>, is the current drawn at device terminals V<sub>DD</sub> and V<sub>SS</sub> for total current through the device. The channel component (V<sub>in</sub>-V<sub>out</sub>)/R<sub>ON</sub>, should not be included.

# MC14551B

## SWITCHING CHARACTERISTICS\* ( $C_L = 50 \text{ pF}$ , $T_A = 25^\circ\text{C}$ )

Characteristic	Symbol	$V_{DD}-V_{SS}$ Vdc	Min	Typ	Max	Unit
Propagation Delay Times Switch Input to Switch Output ( $R_L = 10 \text{ k}\Omega$ ) $t_{PLH}, t_{PHL} = (0.17 \text{ ns/pF}) C_L + 26.5 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.08 \text{ ns/pF}) C_L + 11 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.06 \text{ ns/pF}) C_L + 9.0 \text{ ns}$	$t_{PLH}, t_{PHL}$	5.0 10 15	— — —	35 15 12	90 40 30	ns
Inhibit to Output ( $R_L = 10 \text{ k}\Omega$ ): Output "1" or "0" to High Impedance, or High Impedance to "1" or "0" Level	$t_{PHZ}, t_{PLZ}$ $t_{PZH}, t_{PZL}$	5.0 10 15	— — —	360 160 120	900 375 300	ns
Control Input to Output ( $R_L = 10 \text{ k}\Omega$ )	$t_{PLH}, t_{PHL}$	5.0 10 15	— — —	350 140 100	875 350 250	ns
Sine Wave Distortion ( $R_L = 1 \text{ k}\Omega$ , $f = 1 \text{ kHz}$ )	—	10	—	0.04	—	%
Bandwidth ( $R_L = 1 \text{ k}\Omega$ , $V_{in} = 1/2 (V_{DD} - V_{EE})$ p-p, $20 \text{ Log}_{10} \frac{V_{out}}{V_{in}} = -3 \text{ dB}$ )	BW	10	—	55	—	MHz
Feedthrough Attenuation, Input to Output ( $R_L = 1 \text{ k}\Omega$ , $V_{in} = 1/2 (V_{DD} - V_{EE})$ p-p, $20 \text{ Log}_{10} \frac{V_{out}}{V_{in}} = -50 \text{ dB}$ )	—	10	—	3.0	—	MHz
Channel Separation ( $R_L = 1 \text{ k}\Omega$ , $V_{in} = 1/2 (V_{DD} - V_{EE})$ p-p, $20 \text{ Log}_{10} \frac{V_{out(B)}}{V_{in(A)}} = -50 \text{ dB}$ )	—	10	—	3.0	—	MHz
Feedthrough Control, Input to Output ( $R_1 = 1 \text{ k}\Omega$ , $R_L = 10 \text{ k}\Omega$ , Control/Inhibit $t_r = t_f = 20 \text{ ns}$ )	—	10	—	30	—	mV
Maximum Control Frequency ( $R_L = 1 \text{ k}\Omega$ , $V_{out} = 1/2 V_{in}$ )	—	10	—	10	—	MHz

\*The formulas given are for the typical characteristics only.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit. For proper operation it is recommended that  $V_{in}$  and  $V_{out}$  be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ).

FIGURE 1 – SWITCH CIRCUIT SCHEMATIC

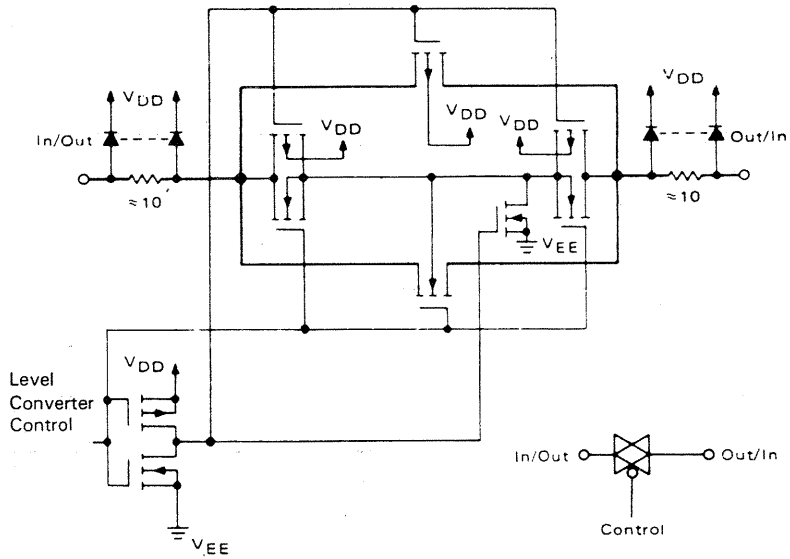
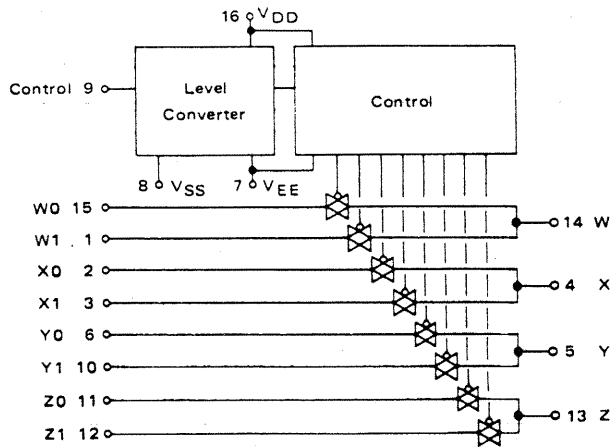


FIGURE 2 – MC14551B FUNCTIONAL DIAGRAM



# MC14551B

## TEST CIRCUITS

FIGURE 3 – INPUT VOLTAGE

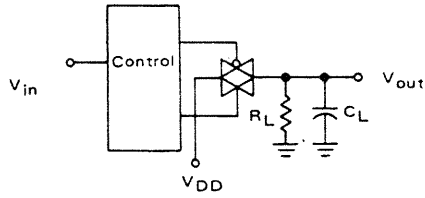


FIGURE 4 – PROPAGATION DELAY TIMES, CONTROL AND INHIBIT TO OUTPUT

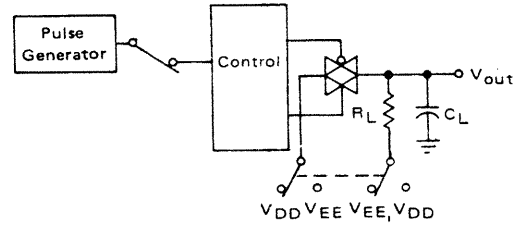


FIGURE 5 – BANDWIDTH AND FEEDTHROUGH ATTENUATION

Control input used to turn ON or OFF the switch under test.

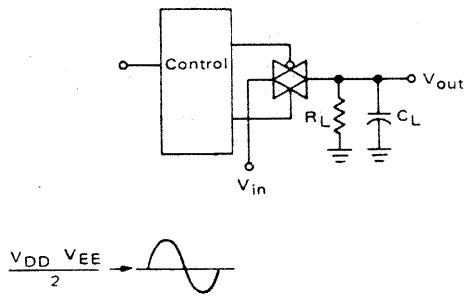


FIGURE 6 – CROSSTALK BETWEEN ANY TWO SWITCHES

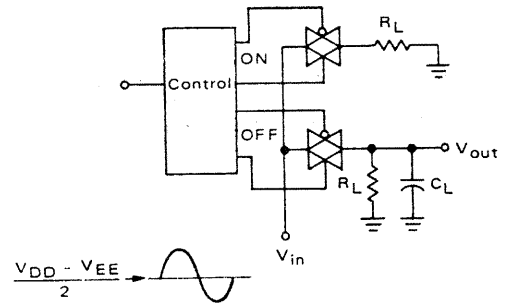


FIGURE 7 – FEEDTHROUGH, CONTROL TO SIGNAL OUTPUT

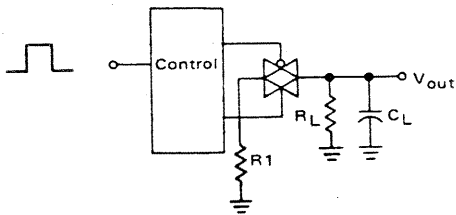


FIGURE 8 – MAXIMUM CONTROL FREQUENCY

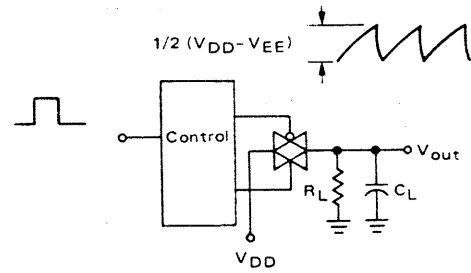
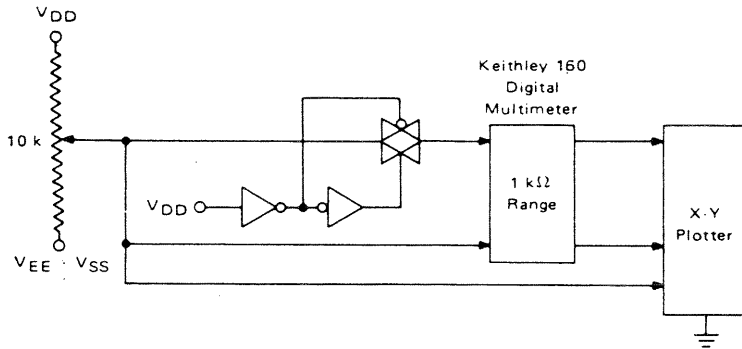


FIGURE 9 – CHANNEL RESISTANCE ( $R_{ON}$ ) TEST CIRCUIT



TYPICAL RESISTANCE CHARACTERISTICS

FIGURE 10 –  $V_{DD}$  @ 7.5 V,  $V_{EE}$  @ -7.5 V

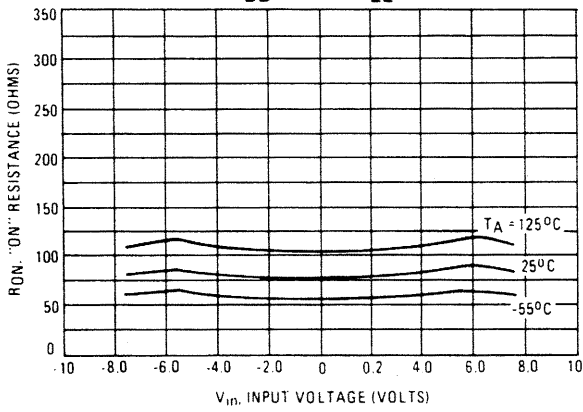


FIGURE 11 –  $V_{DD}$  @ 5.0 V,  $V_{EE}$  @ -5.0 V

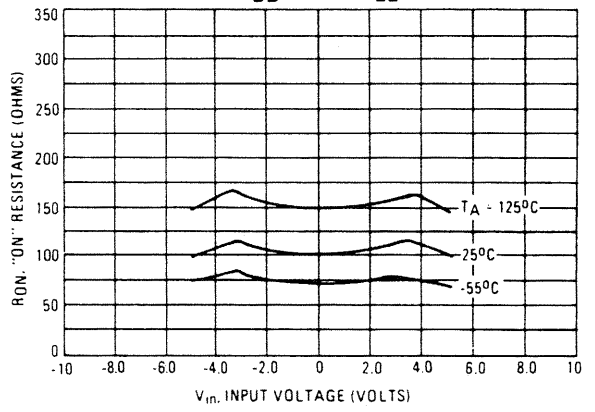


FIGURE 12 –  $V_{DD}$  @ 2.5 V,  $V_{EE}$  @ -2.5 V

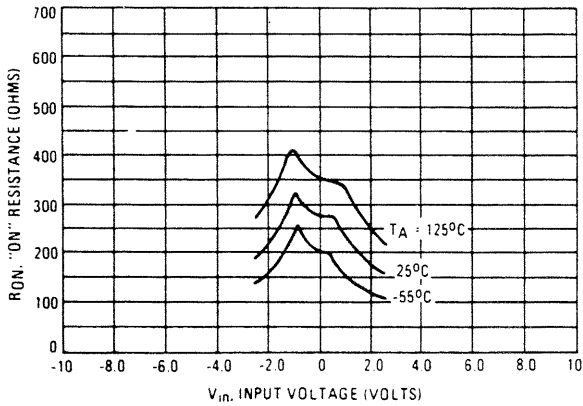


FIGURE 13 – COMPARISON at 25°C,  $V_{DD}$  @  $-V_{EE}$

